

**In the Claims:**

Please cancel claim 27 and amend the claims in the manner indicated.

13. (currently amended) A method of fabricating an integrated circuit chip comprising:  
processing a semiconductor substrate to form a gate array architecture of transistors in the substrate, the gate array architecture comprising a plurality of N-type diffusion regions and P-type diffusion regions; said diffusion regions having partially overlying polysilicon landing sites at least one forming both N-type and P-type transistors;  
wherein the regions are relatively-sized to form two distinct transistor sizes, smaller N- and P-type transistors and larger N- and P-type transistors; and  
wherein said transistors are formed in said gate array architecture so that an interconnect disposed thereon is capable of connecting said smaller transistors to form internal clock buffers.

14. (original) The method of claim 13, wherein said semiconductor substrate comprises a silicon substrate.

15. (currently amended) The method of claim 14, wherein said processing said silicon substrate to form a gate array architecture comprises:  
forming said partially overlying polysilicon landings so that said landings for the smaller and larger transistors are not connected. [[.]]

16. (currently amended) The method of claim 15, wherein ~~the~~ a ratio between the two distinct transistor sizes is on ~~the~~ an order of one-third.

17. (currently amended) The method of claim 16, wherein ~~the~~ a ratio between ~~the~~ capacitance of the larger and smaller relatively sized transistors is on ~~the~~ an order of one-third.

18. (previously presented) The method of claim 15, and further comprising:  
forming an interconnect overlying said gate array architecture.

19. (currently amended) The method of claim 18, wherein said forming an interconnect comprises forming an interconnect that connects the transistors of the [[ ]] gate array architecture to form a flip-flop having internal clock buffers.

20. (currently amended) The method of claim 19, wherein said forming an interconnect comprises forming an interconnect that connects the transistors of the gate array architecture so that the internal clock buffers of the flip-flop are formed from the smaller transistors.

27. (cancelled)